## ABSTRACT

INTEGRATION OF MOM CAPACITOR INTO DUAL DAMASCENE PROCESS

A method for fabricating a metal-oxide-metal capacitor using a dual damascene process is described. A dielectric layer is provided overlying a semiconductor substrate. A dual damascene opening in the dielectric layer is filled with copper to form a copper via underlying a copper line. A first metal layer is deposited overlying the copper line and patterned to form a bottom capacitor plate contacting the copper line. A capacitor dielectric layer is deposited overlying the bottom capacitor plate. A second metal layer is deposited overlying the capacitor dielectric layer and patterned to form a top capacitor plate to complete fabrication of a metal-oxide-metal capacitor.

(FIGURE 3 IS SUGGESTED FOR PUBLICATION)